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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Top View

Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0349				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0385				
I _D (A) per leg	20				
Configuration	Dual				

PowerPAK® SO-8L Dual O J S THE STATE OF THE

Bottom View

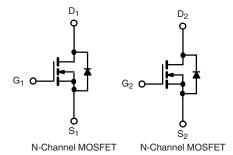
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912









ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ958EP-T1-GE3

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	60			
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	1	20		
	T _C = 125 °C	I _D	12		
Continuous Source Current (Diode Conduct	tion) ^a	I _S	30	Α	
Pulsed Drain Current ^b		I _{DM}	80		
Single Pulse Avalanche Current		I _{AS}	16		
Single Pulse Avalanche Energy	Single Pulse Avalanche Energy		12	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	Pn	35	W	
	T _C = 125 °C	rD	12		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e			260	C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient F	PCB Mount c	R_{thJA}	85	°C/W
Junction-to-Case (Drain)		R_{thJC}	4.3	G/W

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square Pcb (Fr4 material).
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.

Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$		1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
-		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	1
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
		V _{GS} = 10 V	I _D = 4.5 A	-	0.0291	0.0349	
Dunin Course On Chata Basistana 3		V _{GS} = 10 V	I _D = 4.5 A, T _J = 125 °C	-	-	0.0610	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.5 A, T _J = 175 °C	-	-	0.0710	Ω
		V _{GS} = 4.5 V	I _D = 4.3 A	-	0.0319	0.0385	
Forward Transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 4.5 A	-	36	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	857	1075	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	77	100	pF
Reverse Transfer Capacitance	C _{rss}			-	35	45	
Total Gate Charge ^c	Qg			-	15	23	
Gate-Source Charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_D = 4.5 \text{ A}$	-	2.6	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	2.7	-	
Gate Resistance	R_g		f = 1 MHz	1	2.15	3.6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	5	8	
Rise Time ^c	t _r	V _{DD} :	= 30 V, $R_L = 30 \Omega$	-	12	18	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 1 \text{ A}, Y$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	18	27	ns
Fall Time ^c	t _f	1		-	7	11	
Source-Drain Diode Ratings and Chara	cteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	80	Α
Forward Voltage	V _{SD}	I ₋ -	3.2 A, V _{GS} = 0 V	_	0.8	1.1	V

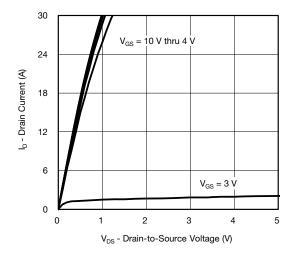
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

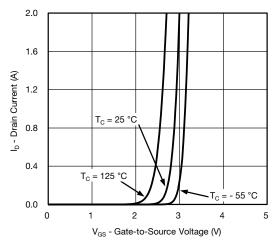
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



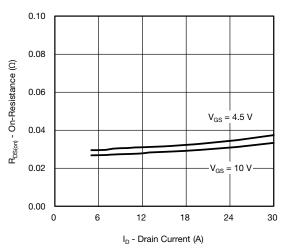
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



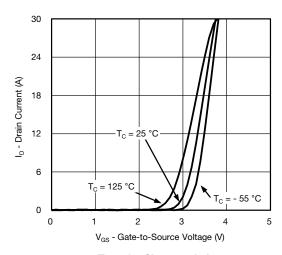
Output Characteristics



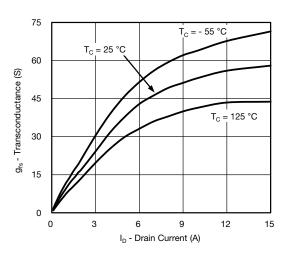
Transfer Characteristics



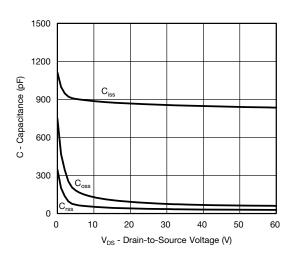
On-Resistance vs. Drain Current



Transfer Characteristics



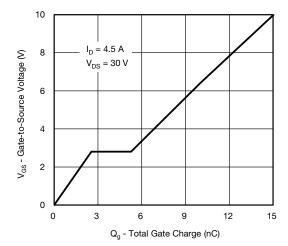
Transconductance



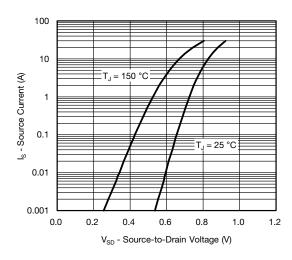
Capacitance



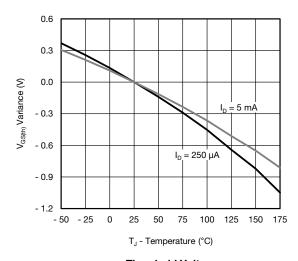
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



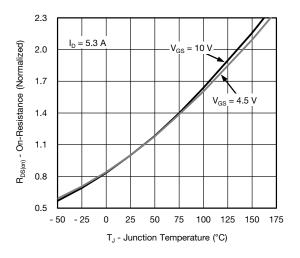
Gate Charge



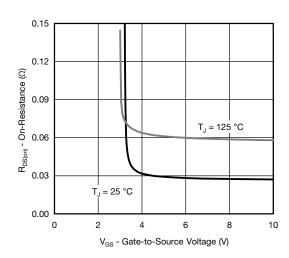
Source Drain Diode Forward Voltage



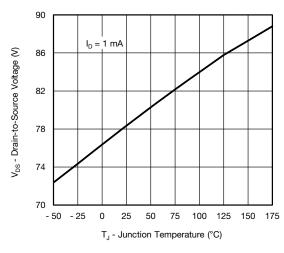
Threshold Voltage



On-Resistance vs. Junction Temperature



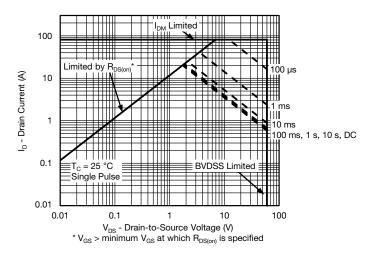
On-Resistance vs. Gate-to-Source Voltage



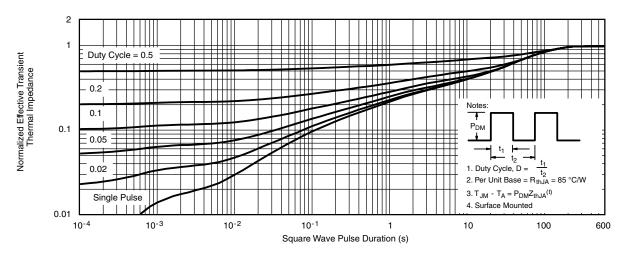
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



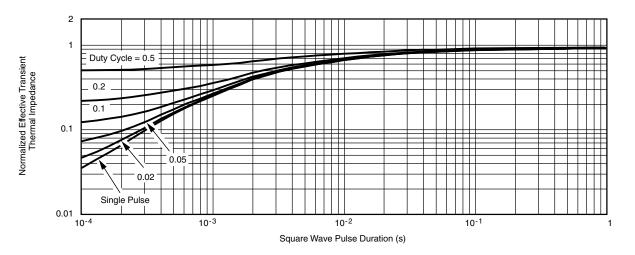
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

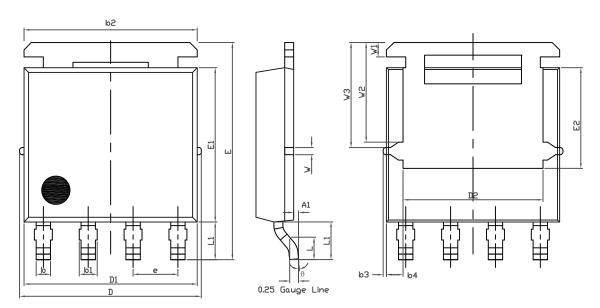
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

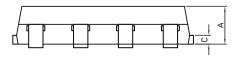
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?62513.

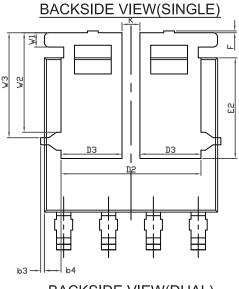
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PowerPAK® SO-8L Case Outline for Al Parts



TOPSIDE VIEW





BACKSIDE VIEW(DUAL)



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DIM	MILLIMETERS				INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96			0.117			
q	0°	-	10°	0°	-	10°	

ECN: C15-1203-Rev. A, 07-Sep-15

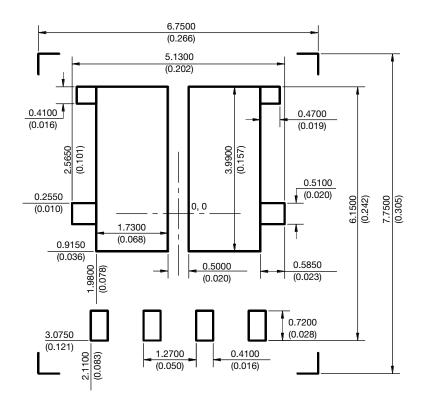
DWG: 6044

Note

· Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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